

Silicon Nitride properties

Property	Value	Units
DC resistivity	1E14	Ohm – cm @ 25 Deg C
Density	3.1	g-cm ³
Dielectric constant	7.5	-
Dielectric strength	1E7	V/cm
Energy gap	5.0 (approx)	eV
Etch rate in buffered HF	5 – 10	Ang/min
Infrared absorption band	11.5 – 12.0	um
Refractive index	2.05	-
Stress on film on silicon	9.0 – 10.0 E14	Dynes/cm ²

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